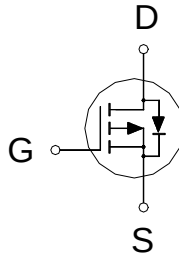
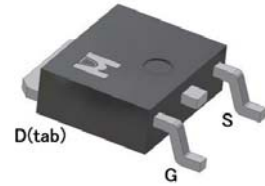




P-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV_{DSS}	-30V
$R_{DS(on)} (MAX.)$	50m Ω
I_D	-10A



UIS, Rg 100% Tested

Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^{\circ}\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	-10	A
	$T_C = 100\text{ }^{\circ}\text{C}$		-7	
Pulsed Drain Current ¹		I_{DM}	-40	
Avalanche Current		I_{AS}	-10	
Avalanche Energy	$L = 0.1\text{mH}$, $I_D = -10\text{A}$, $R_G = 25\Omega$	E_{AS}	5	mJ
Repetitive Avalanche Energy ²	$L = 0.05\text{mH}$	E_{AR}	2	
Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	P_D	30	W
	$T_C = 100\text{ }^{\circ}\text{C}$		12	
Operating Junction & Storage Temperature Range		T_{j} , T_{stg}	-55 to 150	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		4.1	$^{\circ}\text{C} / \text{W}$
Junction-to-Ambient	$R_{\theta JA}$		80	

¹Pulse width limited by maximum junction temperature.

²Duty cycle $\leq 1\%$



ELECTRICAL CHARACTERISTICS ($T_c = 25\text{ }^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0	-1.5	-3.0	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -24V, V_{GS} = 0V$			-1	μA
		$V_{DS} = -20V, V_{GS} = 0V, T_J = 125\text{ }^{\circ}C$			-25	
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = -5V, V_{GS} = -10V$	-10			A
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = -10V, I_D = -6A$		43	50	m Ω
		$V_{GS} = -5V, I_D = -3A$		60	75	
Forward Transconductance ¹	g_{fs}	$V_{DS} = -5V, I_D = -6A$		5		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = -15V, f = 1MHz$		820		pF
Output Capacitance	C_{oss}			122		
Reverse Transfer Capacitance	C_{rss}			97		
Gate Resistance	R_g	$V_{GS} = 15mV, V_{DS} = 0V, f = 1MHz$		4.5		Ω
Total Gate Charge ^{1,2}	Q_g	$V_{DS} = -10V, V_{GS} = -10V,$ $I_D = -6A$		9		nC
Gate-Source Charge ^{1,2}	Q_{gs}			2.2		
Gate-Drain Charge ^{1,2}	Q_{gd}			2.5		
Turn-On Delay Time ^{1,2}	$t_{d(on)}$	$V_{DS} = -10V,$ $I_D = -1A, V_{GS} = -10V, R_{GS} = 6\Omega$		12		nS
Rise Time ^{1,2}	t_r			16		
Turn-Off Delay Time ^{1,2}	$t_{d(off)}$			30		
Fall Time ^{1,2}	t_f			20		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T _C = 25 °C)						
Continuous Current	I_S				-10	A
Pulsed Current ³	I_{SM}				-40	
Forward Voltage ¹	V_{SD}	$I_F = I_S, V_{GS} = 0V$			1.3	V
Reverse Recovery Time	t_{rr}	$I_F = -5A, dI_F/dt = 100A / \mu S$		15		nS
Reverse Recovery Charge	Q_{rr}			8		nC

¹Pulse test : Pulse Width $\leq 300\text{ }\mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

³Pulse width limited by maximum junction temperature.

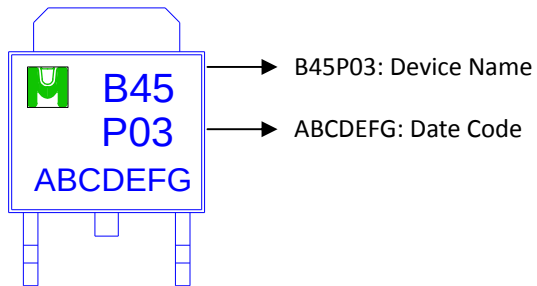


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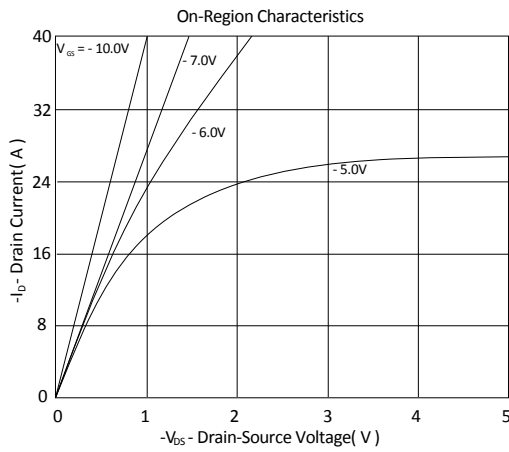
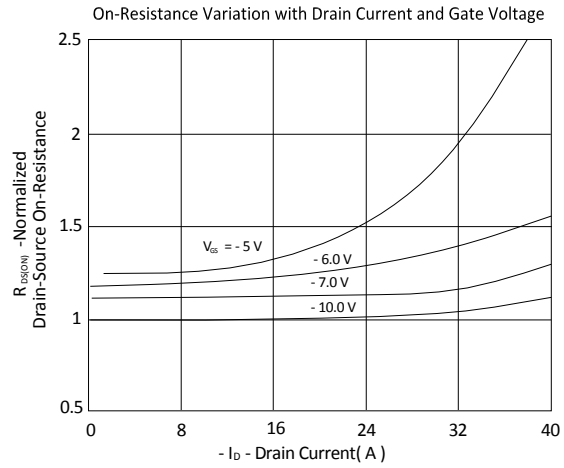
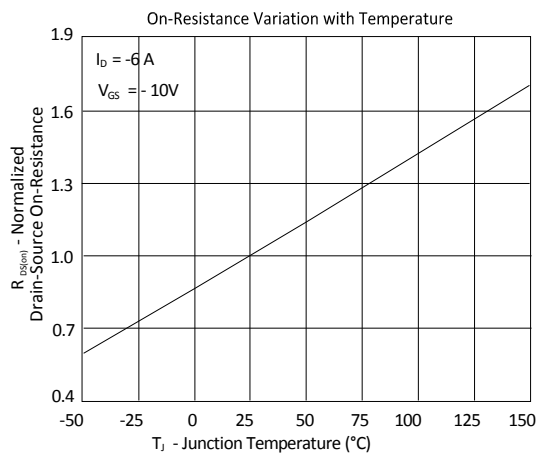
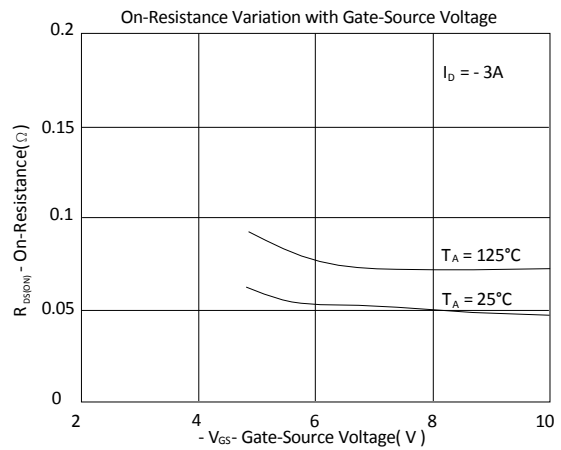
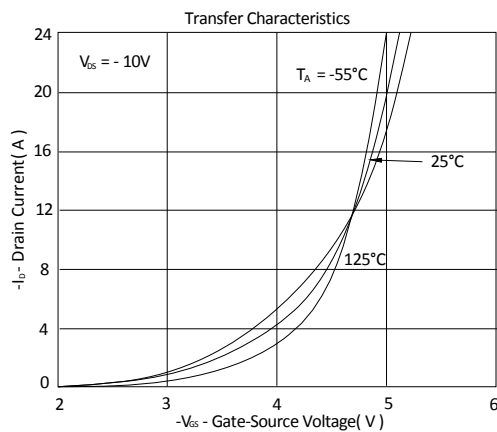
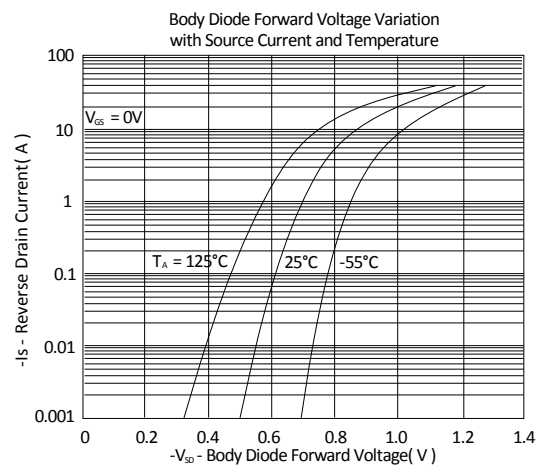
EMB45P03A

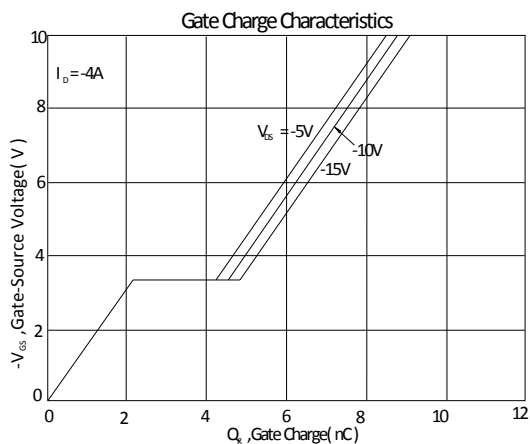
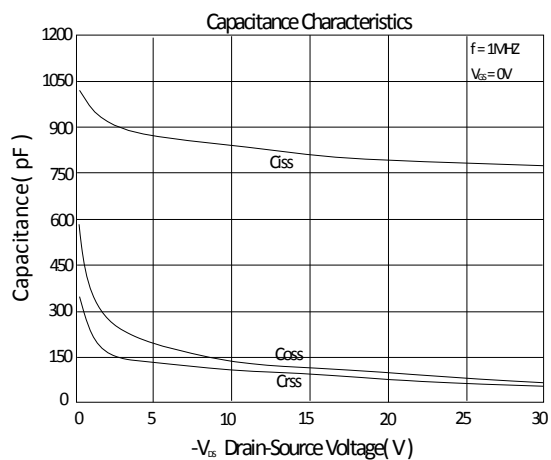
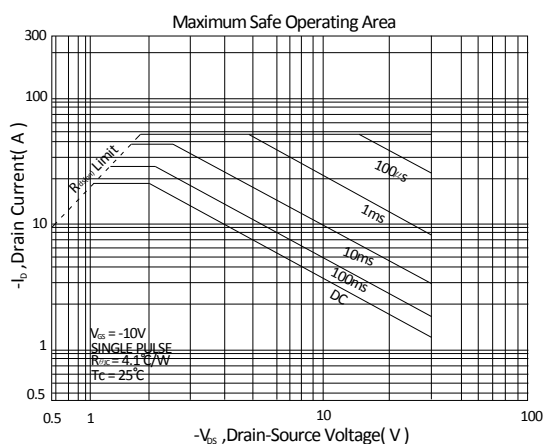
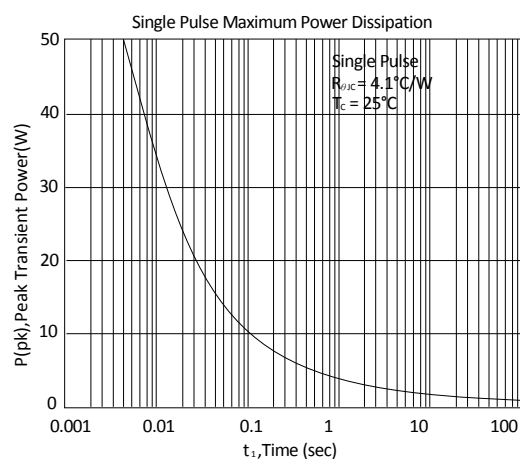
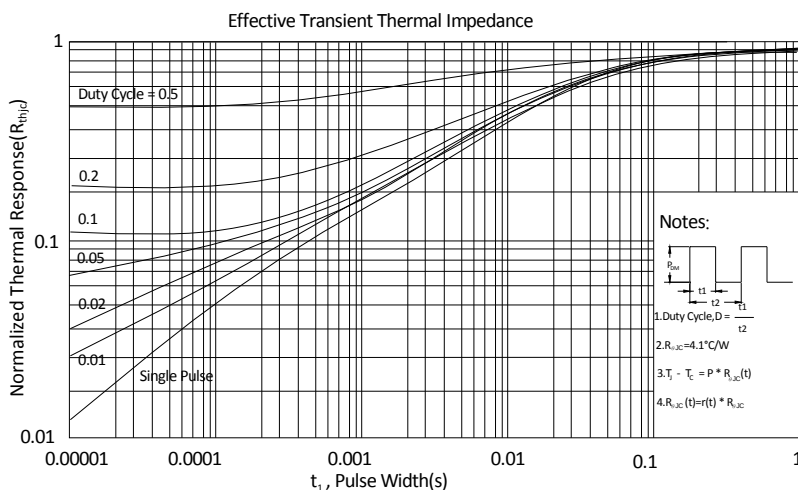
Ordering & Marking Information:

Device Name: EMB45P03A for DPAK (TO-252)



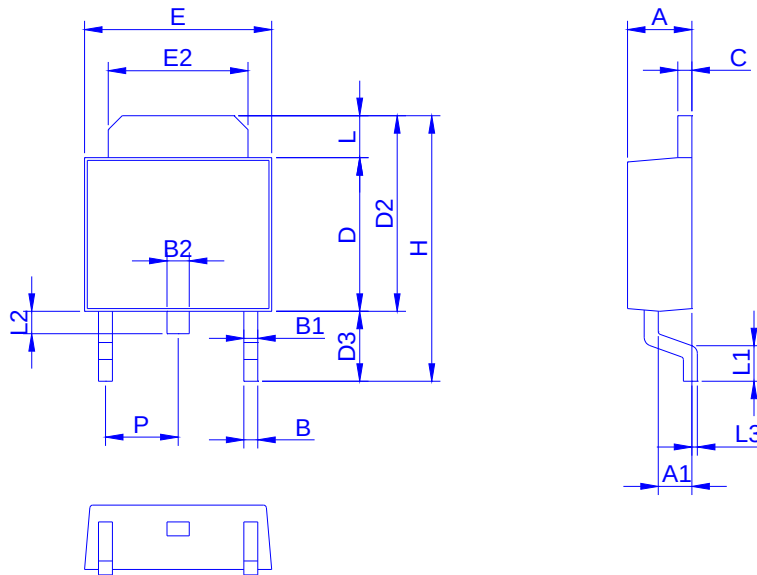
TYPICAL CHARACTERISTICS







Outline Drawing



Dimension	A	A1	B	B1	B2	C	D	D2	D3	E	E2	H	L	L1	L2	L3	P
Min.	2.10	0.95	0.30	0.40	0.60	0.40	5.30	6.70	2.20	6.40	4.80	9.20	0.89	0.90	0.50	0.00	2.10
Max.	2.50	1.30	0.85	0.94	1.00	0.60	6.20	7.30	3.00	6.70	5.45	10.15	1.70	1.65	1.10	0.30	2.50

Footprint

